

# Updated Results from the SLAC ESTB T-506 Irradiation Study

SiD Workshop  
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# T-506 Motivation

BeamCal maximum dose ~100 MRad/yr

BeamCal is sizable: ~2 m<sup>2</sup> of sensors.

A number of ongoing studies with novel sensors: GaAs, CVD diamond

→ Are these radiation tolerant?

→ Also, might mainstream Si sensors be of use?

Some reasons for optimism for Si...

# Hadronic Processes in EM Showers

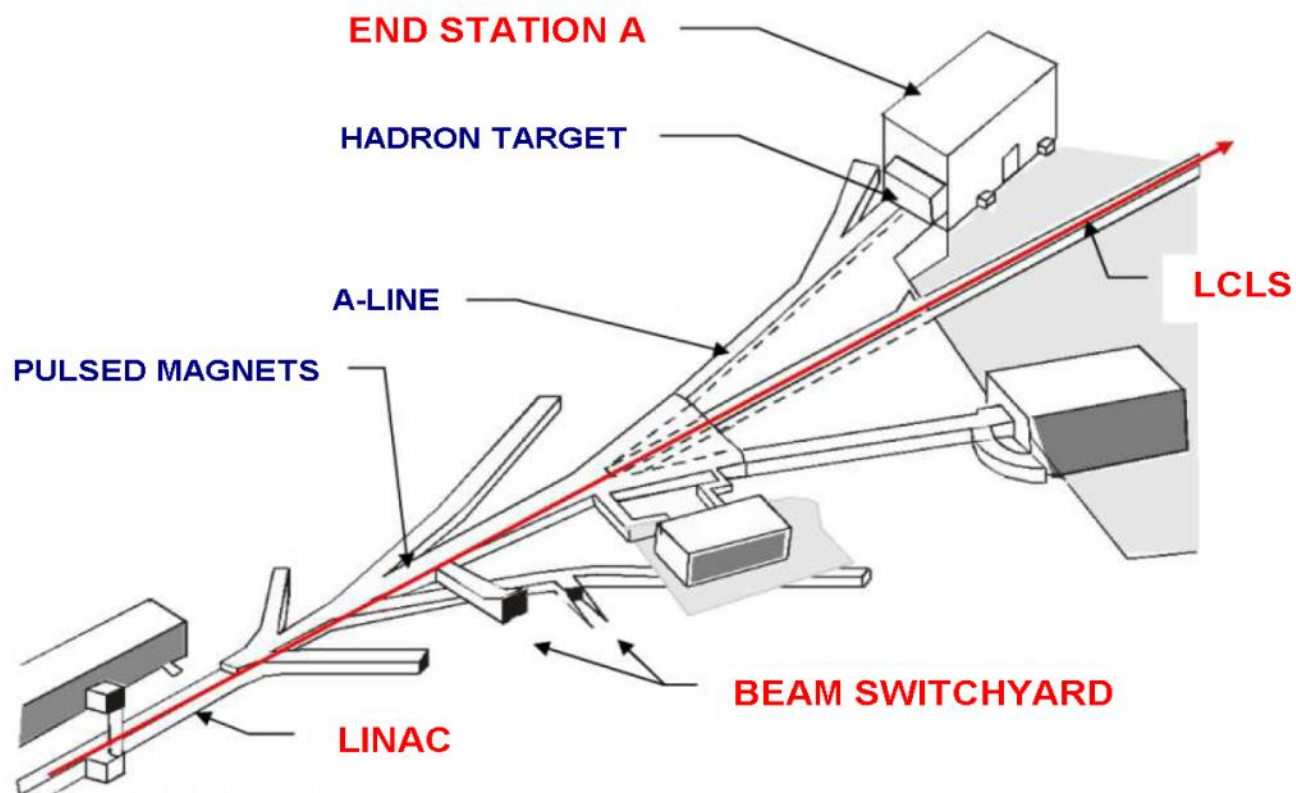
There seem to be three main processes for generating hadrons in EM showers (all induced by **photons**):

- Nuclear (“giant dipole”) resonances  
Resonance at 10-20 MeV ( $\sim E_{\text{critical}}$ )
  - Photoproduction  
Threshold seems to be about 200 MeV
  - Nuclear Compton scattering  
Threshold at about 10 MeV;  $\Delta$  resonance at 340 MeV
- These are largely isotropic; must have most of hadronic component develop near sample

# Irradiating the Sensors

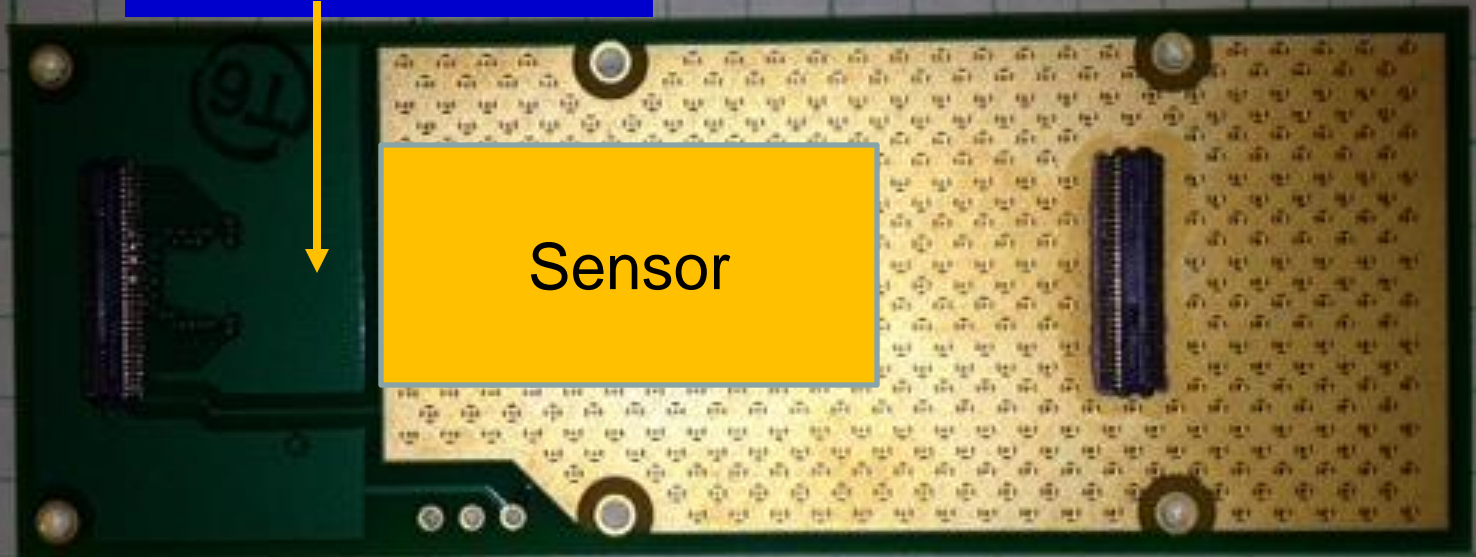
# LCLS and ESA

Use pulsed magnets in the beam switchyard to send beam in ESA.



# Daughter Board Assembly

Pitch adapter,  
bonds



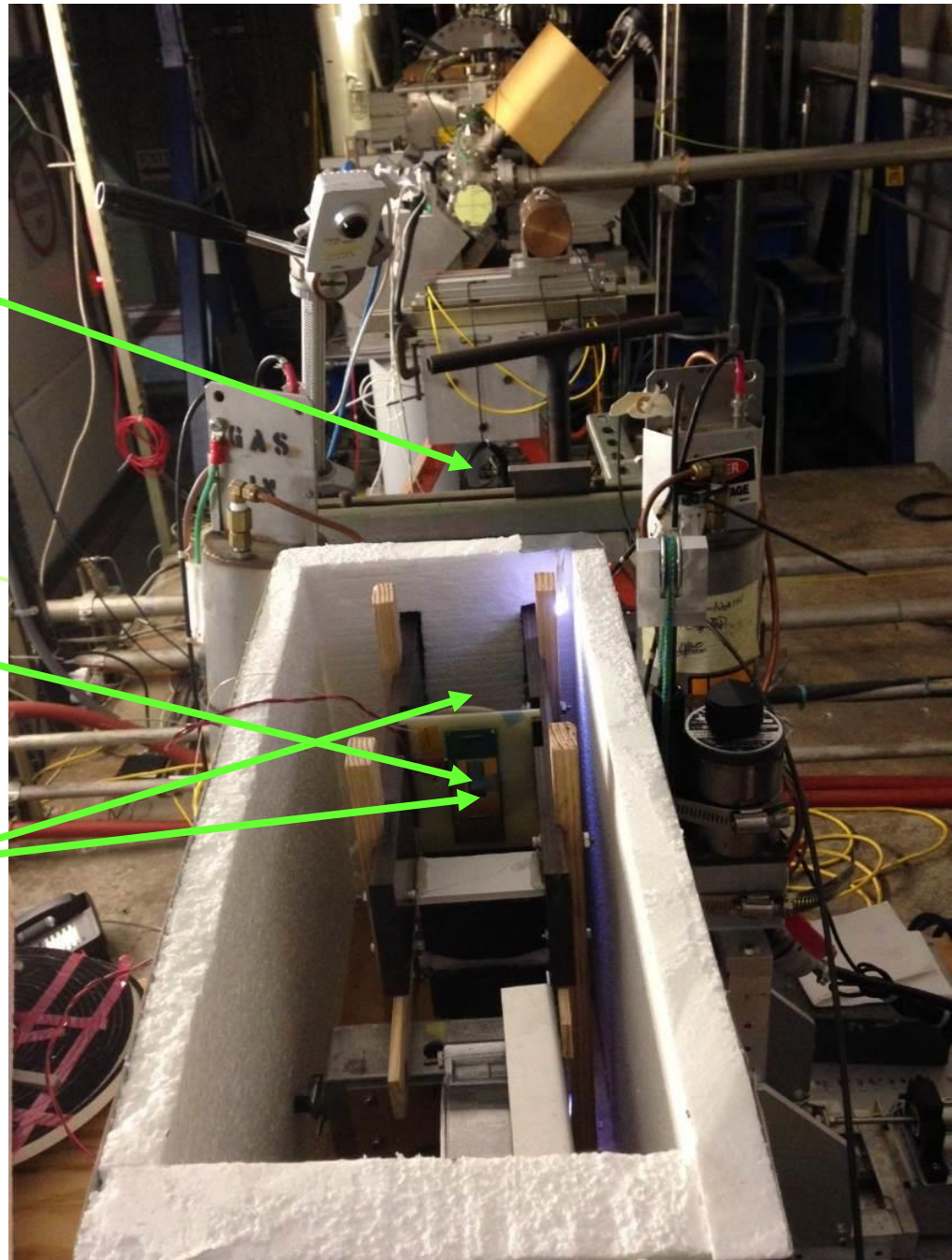
Sensor

1 inch

2  $X_0$  pre-radiator;  
introduces a little  
divergence in  
shower


Sensor sample

Not shown: 4  $X_0$   
and 8  $X_0$  radiators  
just before and after  
sensor



# Dose Rates (Including 1 cm<sup>2</sup> Rastering)

Mean fluence per  
incident e<sup>-</sup>



Electron Energy (GeV)	Shower Conversion Factor $\alpha$	Dose per nC Delivered Charge (kRad)
2	2.1	0.34
4	9.4	1.50
6	16.5	2.64
8	23.5	3.76
10	30.2	4.83
12	36.8	5.89

**Confirmed  
with RADFET  
to within 10%**

**Maximum dose rate (10.6 GeV; 10 Hz; 150 pC per pulse):**

**28 Mrad per hour**



# T506 Si Doses

“P” = p-type

“N” = n-type

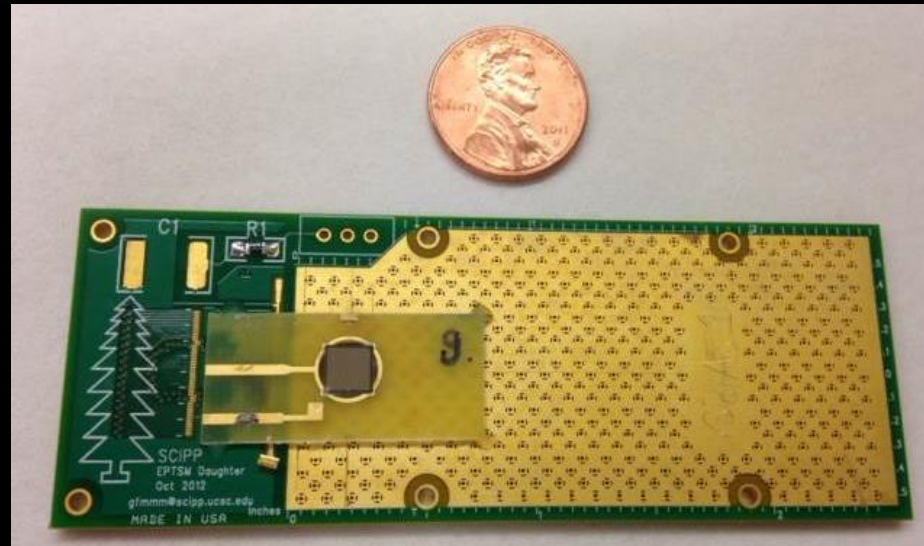
“F” = float zone

“C” = Czochralski

Sensor	$V_{FD}$	Irradiation Temp. (C)	Beam Energy (GeV)	Delivered Charge ( $\mu\text{C}$ )	Dose (MRad)
PF05	190	0	5.88	2.00	5.13
PF14	190	0	3.48	16.4	19.7
PC10	660	0	5.88	1.99	5.12
PC08	700	0	(5.88, 4.11, 4.18)	(3.82,3.33,3.29)	20.3
NF01	90	0	4.18	2.30	3.68
NF02	90	0	4.02	12.6	19.0
NF07	100	5	8.20	23.6	91.4
NC01	220	0	5.88	2.00	5.13
NC10	220	0	3.48	15.1	18.0
NC03	220	5	4.01	59.9	90.2
NC02	220	5*	(10.60,8.20)	(32.3,13.8)	220

# T506 GaAs Doses

New this year: GaAs pad sensors via  
Georgy Shelkov, JINR Dubna



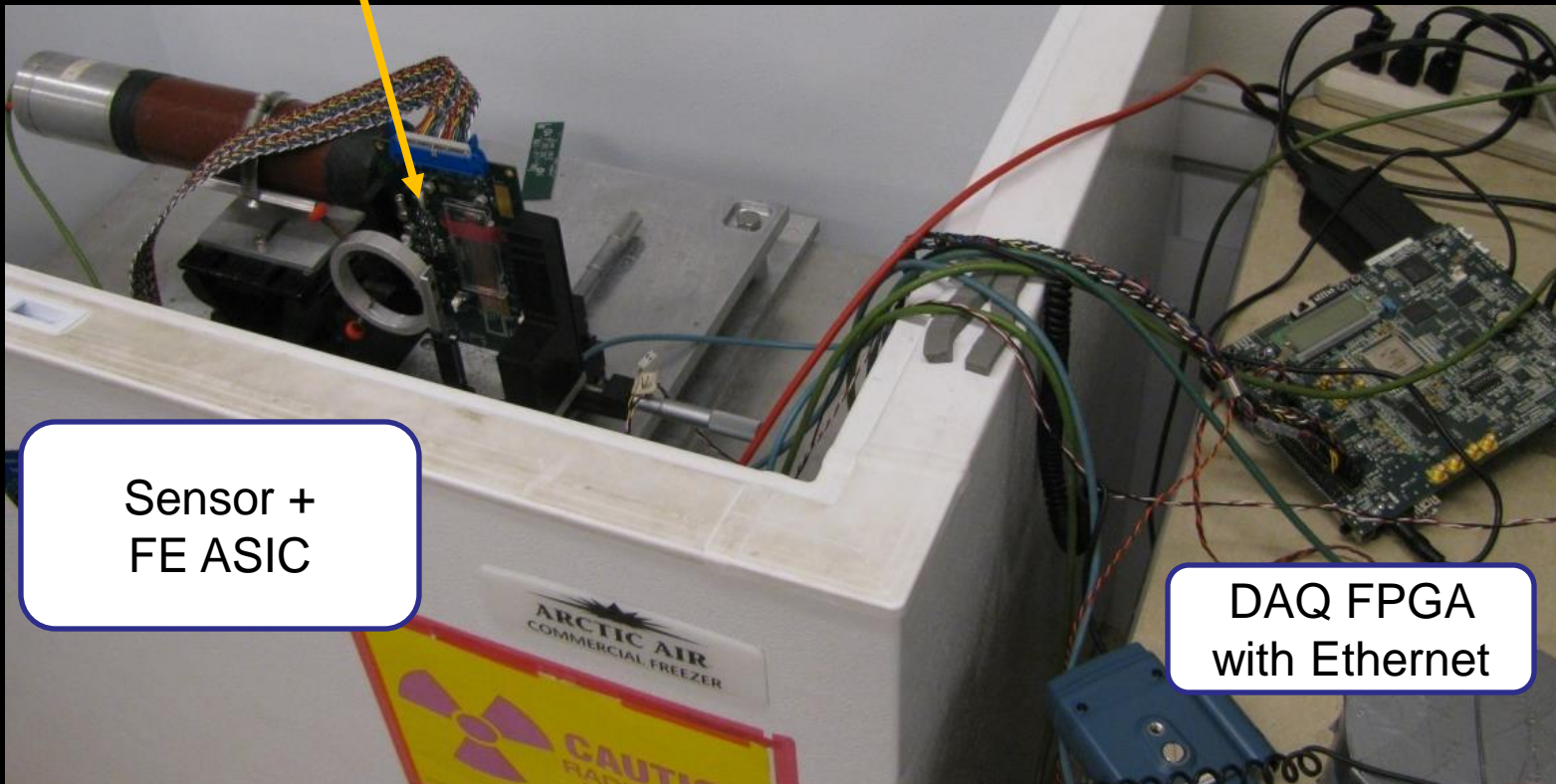
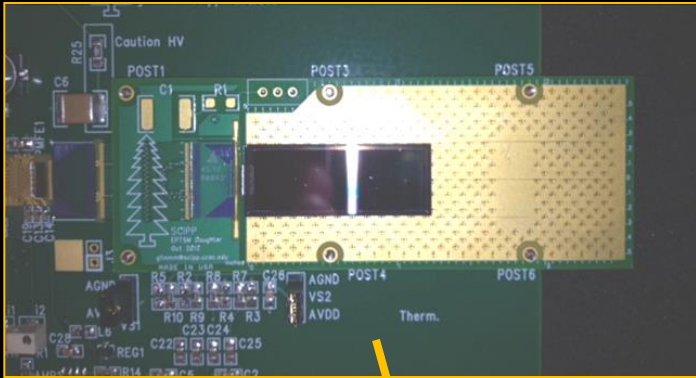
Irradiated with 5.7 and 21.0 Mrad doses of  
electromagnetically-induced showers

Irradiation temperature 3°C; samples held  
and measured at -15°C

# Assessing the Radiation Damage

# Charge Collection Apparatus

- Readout: 300 ns



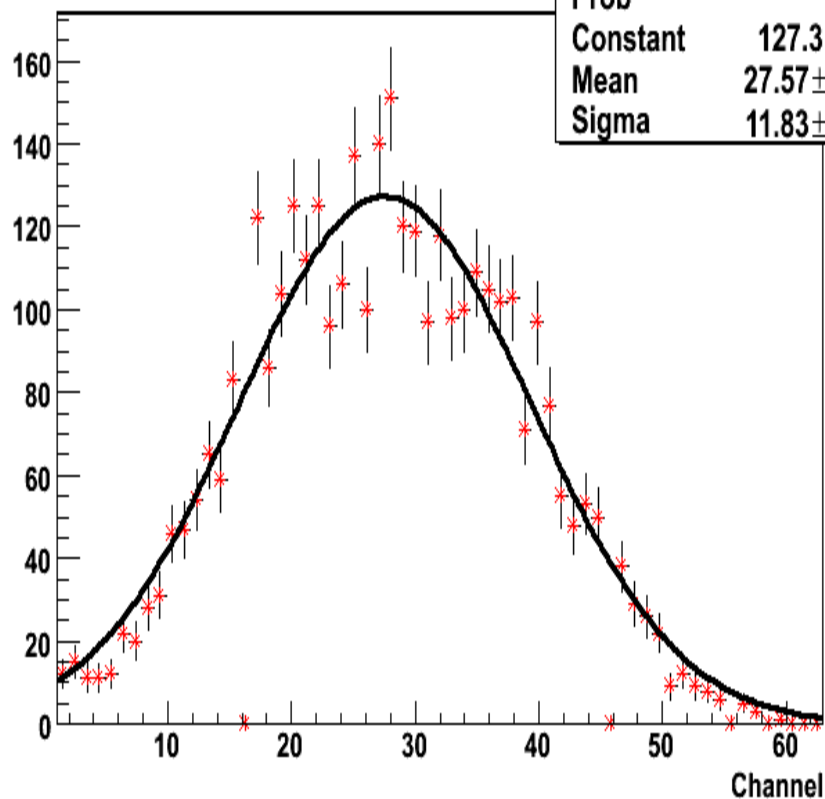
Sensor +  
FE ASIC

DAQ FPGA  
with Ethernet

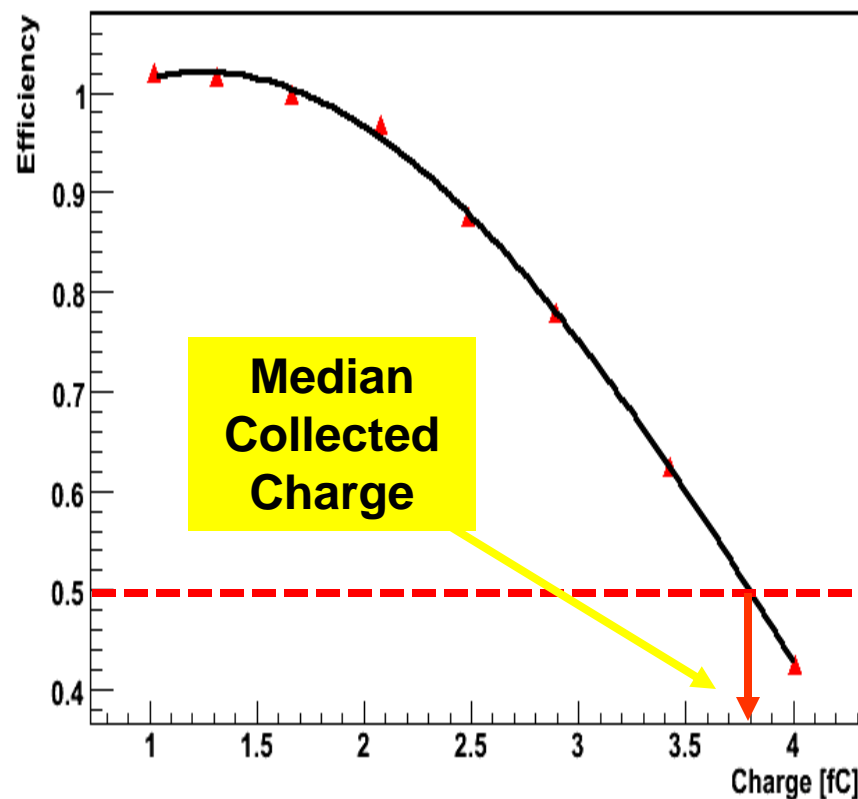
# Charge Collection Measurement

## 2.3 MeV e<sup>-</sup> through sensor into scintillator

Coincidence Profile



Charge Collection Efficiency vs. Threshold : Bias = 200 [V]

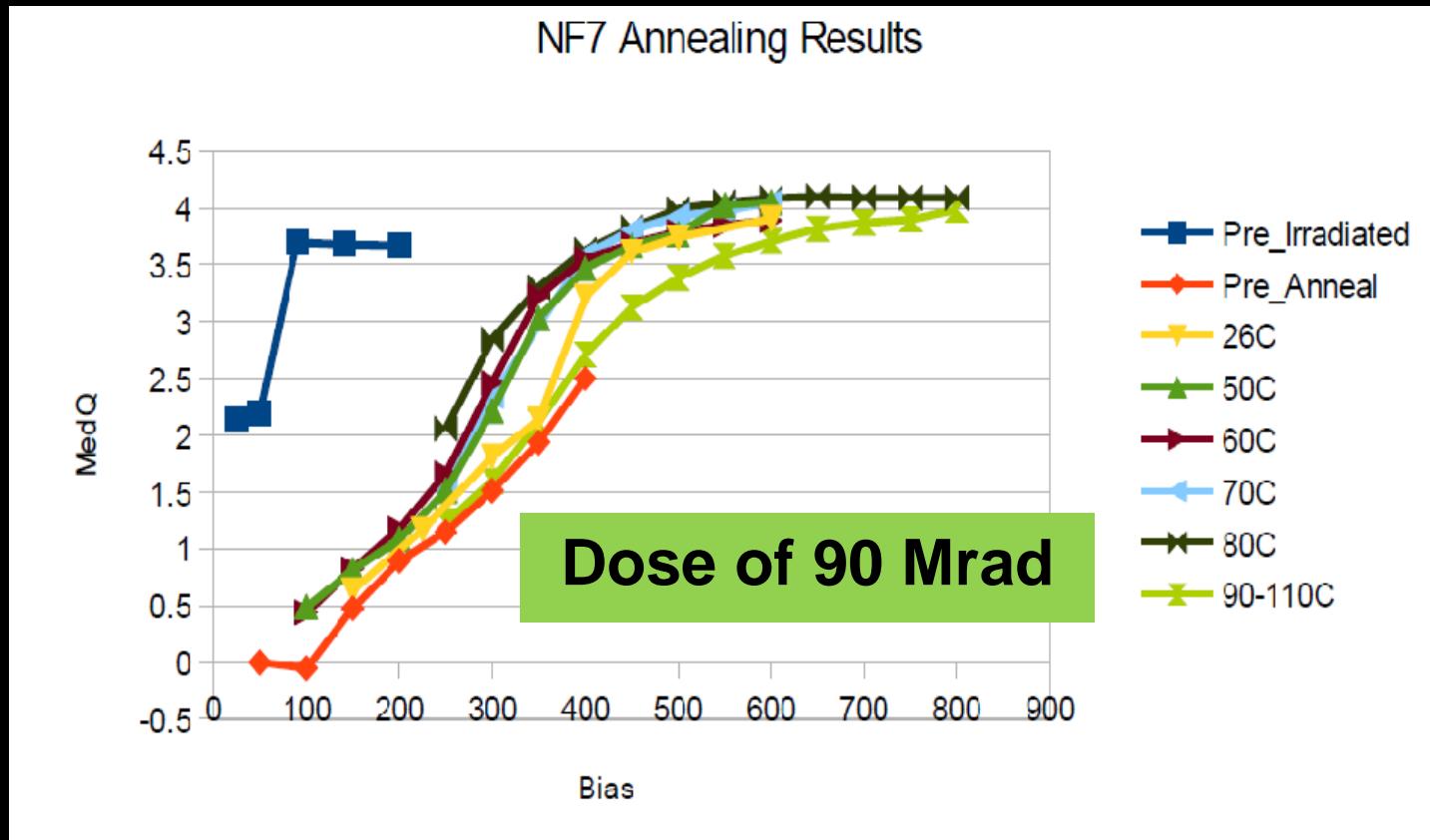


Channel-over-threshold profile

Efficiency vs. threshold

# Results

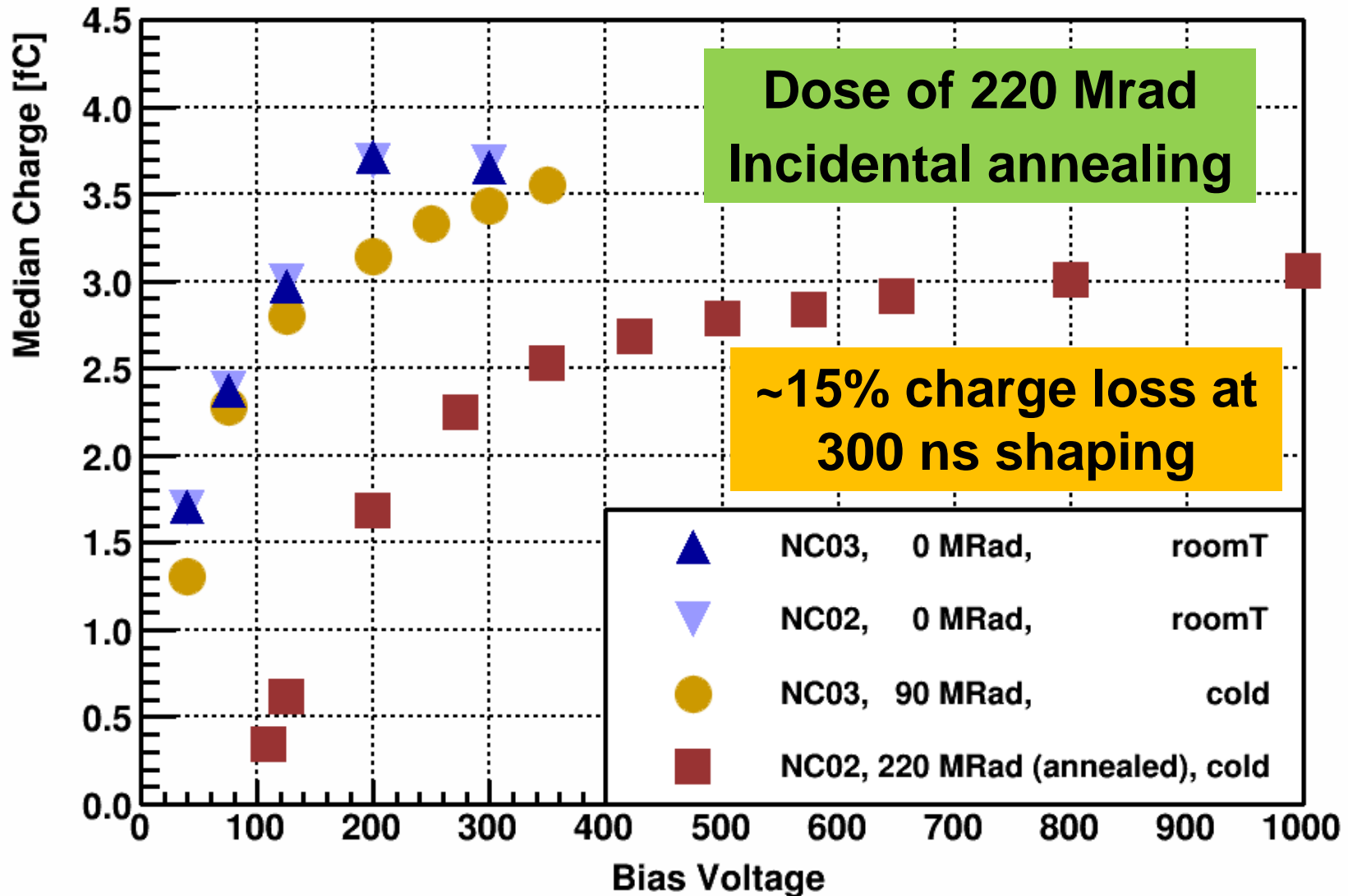
# Results: NF Sensor to 90 Mrad, Plus Annealing Study



Limited beneficial annealing to 90°C  
(reverse annealing above 100°C?)

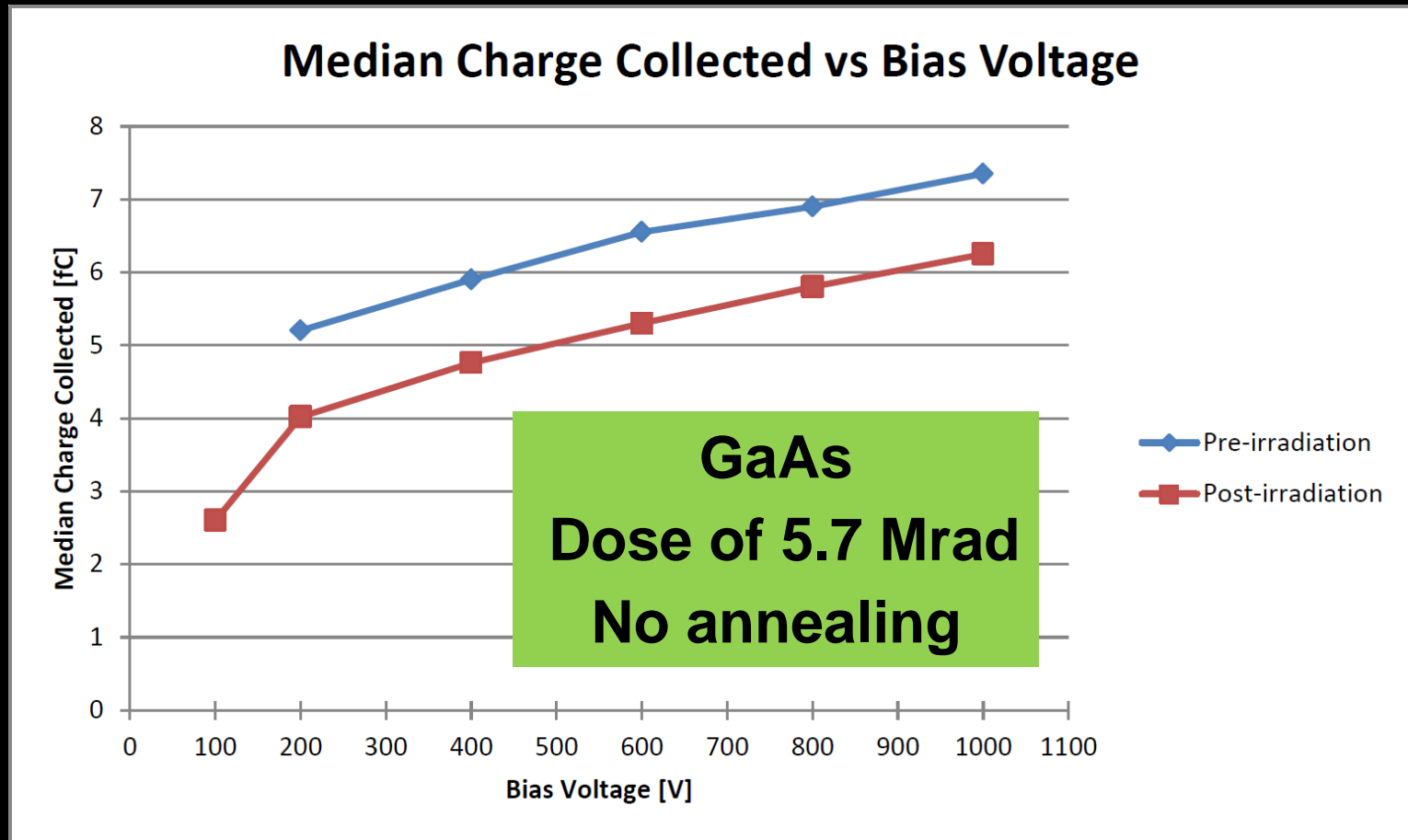
# Results: NC sensors

Median Charge vs Bias Voltage, N-type Magnetic Czochalski sensors



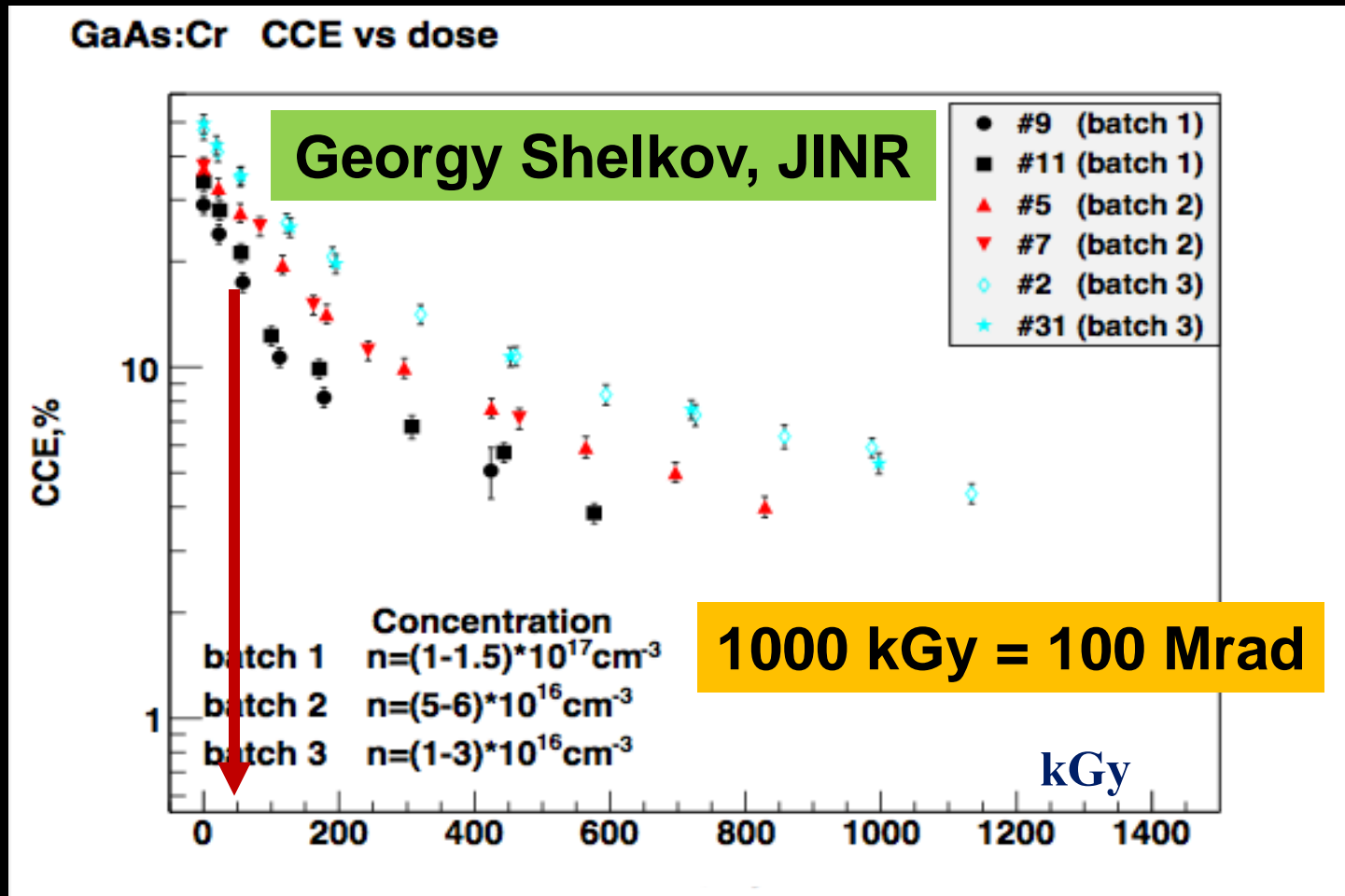


# GaAs Charge Collection after 5.7 Mrad Exposure



**15-20% charge loss at 300 ns shaping**

# Compare to Direct Electron Radiation Results (no EM Shower)



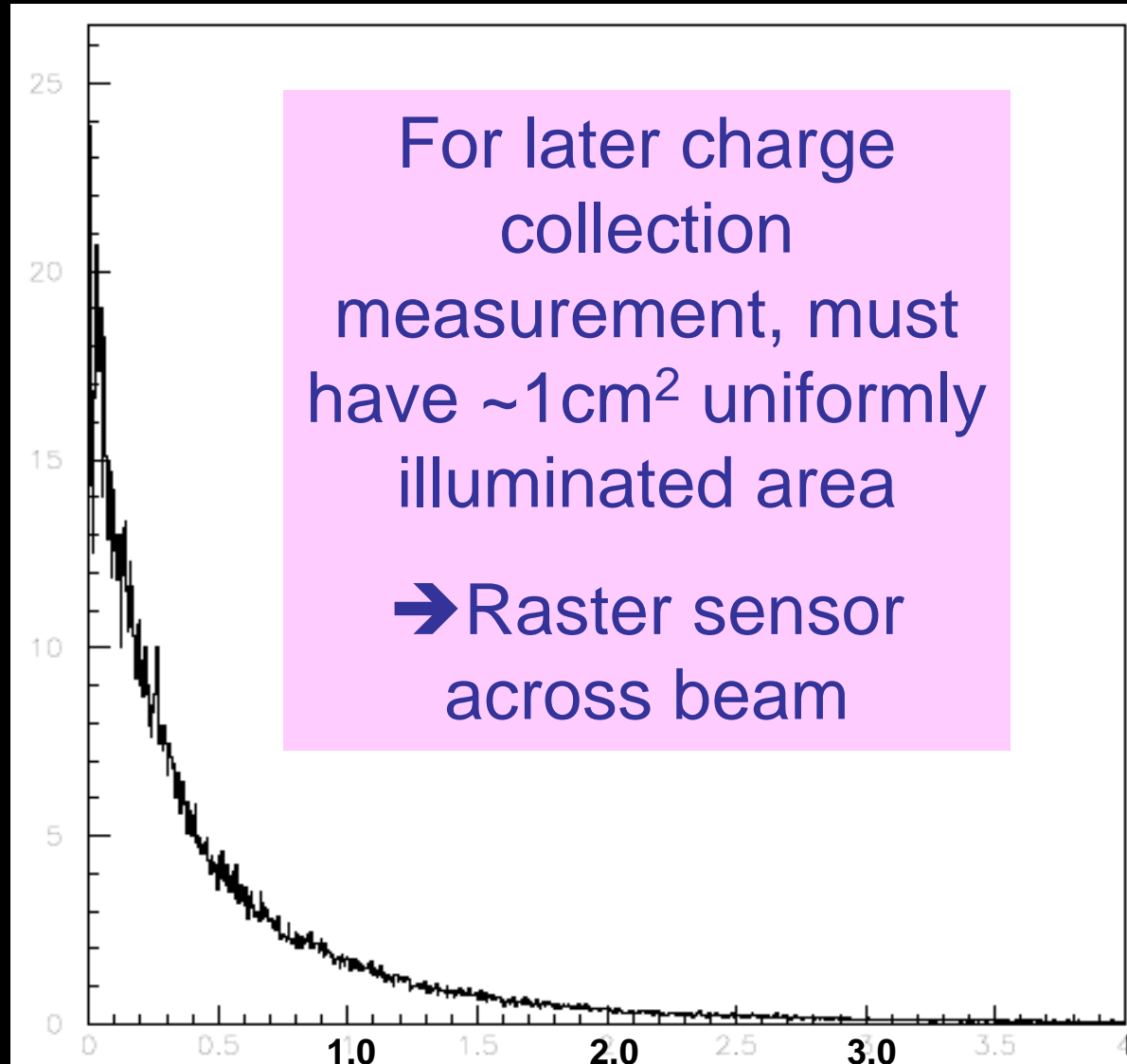
Roughly consistent with direct result

# Summary and Conclusions

- In midst of a program of study of radiation damage in a realistic EM shower environment
- Have irradiated and several Si sensors to as much as 220 Mrad, and GaAs to 20 Mrad.
- Si sensors show some promise to survive the BeamCal integrated dose
- GaAs shows charge loss at 6 Mrad, but still need to do annealing studies (underway)
- Will soon explore 21 Mrad GaAs sensor and do annealing studies on both GaAs sensors
- Expect to run at higher fluence in 2015

# Detector Fluence Distribution (per incident $e^-$ )

Fluence (particles per  $\text{cm}^2$ )



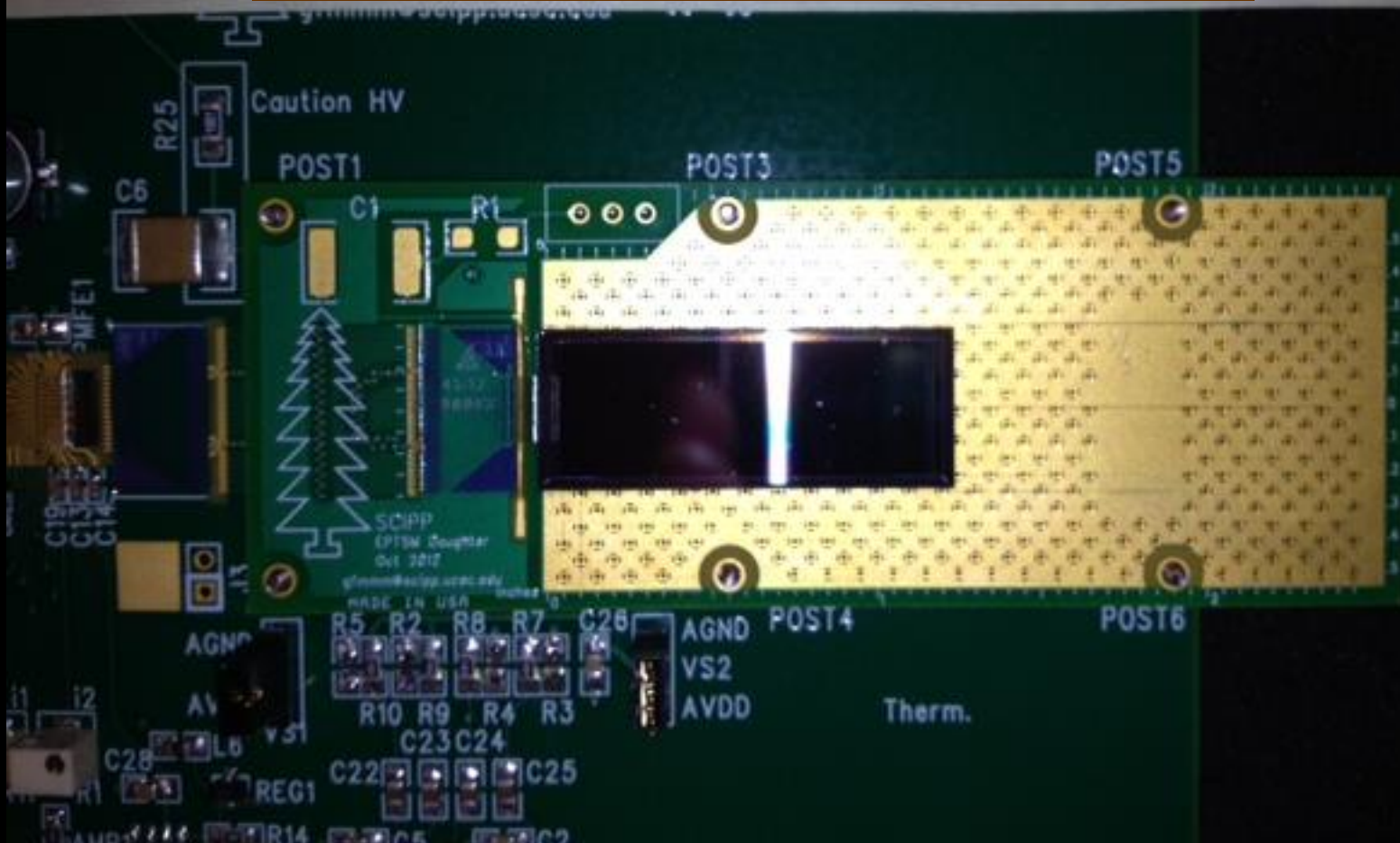
Radius (cm)

# ESTB parameters

Table 1.1.1. ESTB primary electron beam parameters and experimental area at the BSY and in ESA

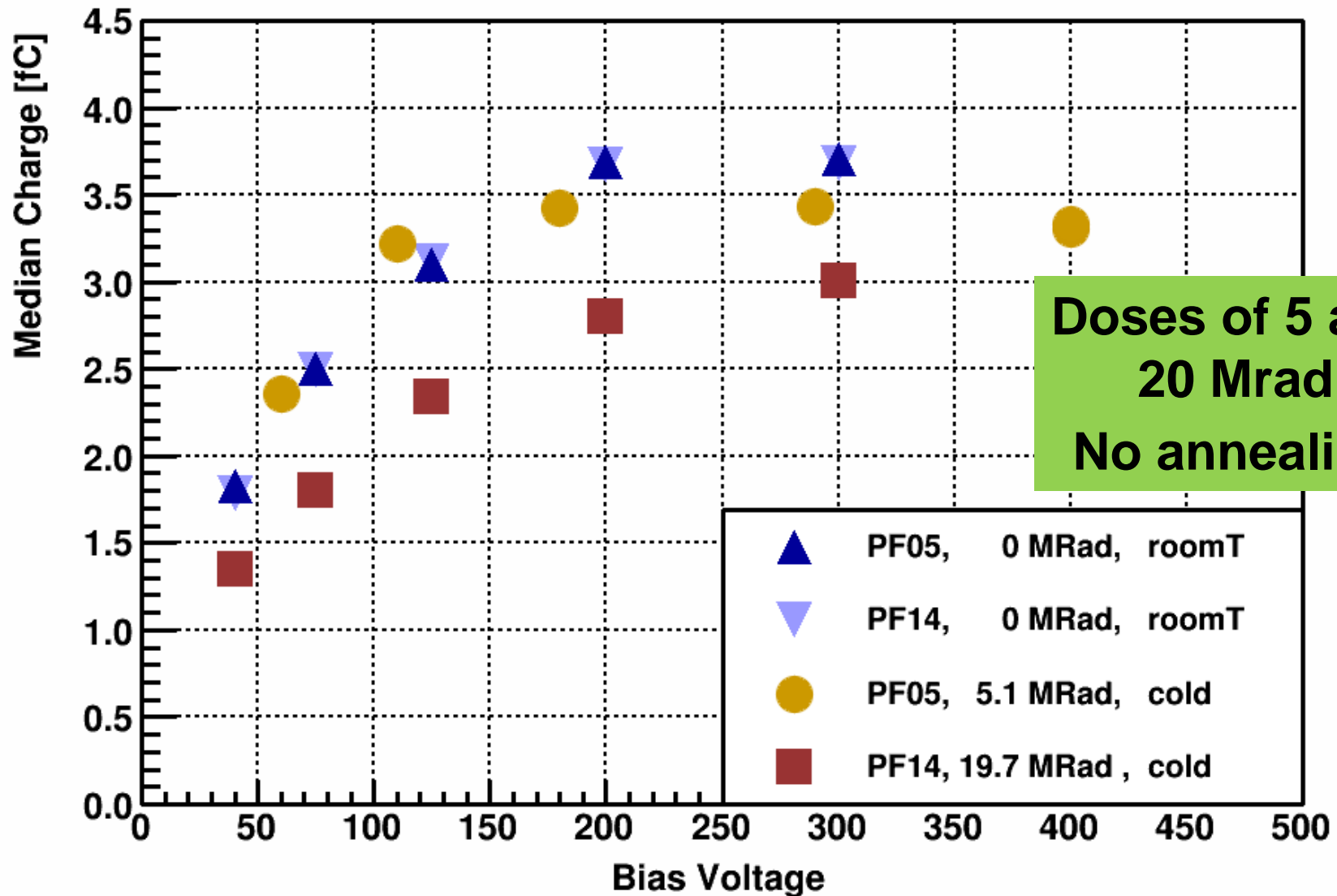
Parameters		ESA
Energy	3.5-10.5 (for now)	<del>15 GeV</del>
Repetition Rate	Up to 10 Hz!	5 Hz
Charge per pulse	$\leq 0.15$ nC	<del>0.35 nC</del>
Energy spread, $\sigma_E / E$		0.02%
Bunch length rms		100 $\mu\text{m}$
Emittance rms ( $\gamma\epsilon_x, \gamma\epsilon_y$ )		(4, 1) $10^{-6}$ m-rad
Spot size at waist ( $\sigma_{x,y}$ )		$< 10$ $\mu\text{m}$
Drift Space available for experimental apparatus		60 m
Transverse space available for experimental apparatus		5 x 5 m

# Daughter/Readout Board Assembly



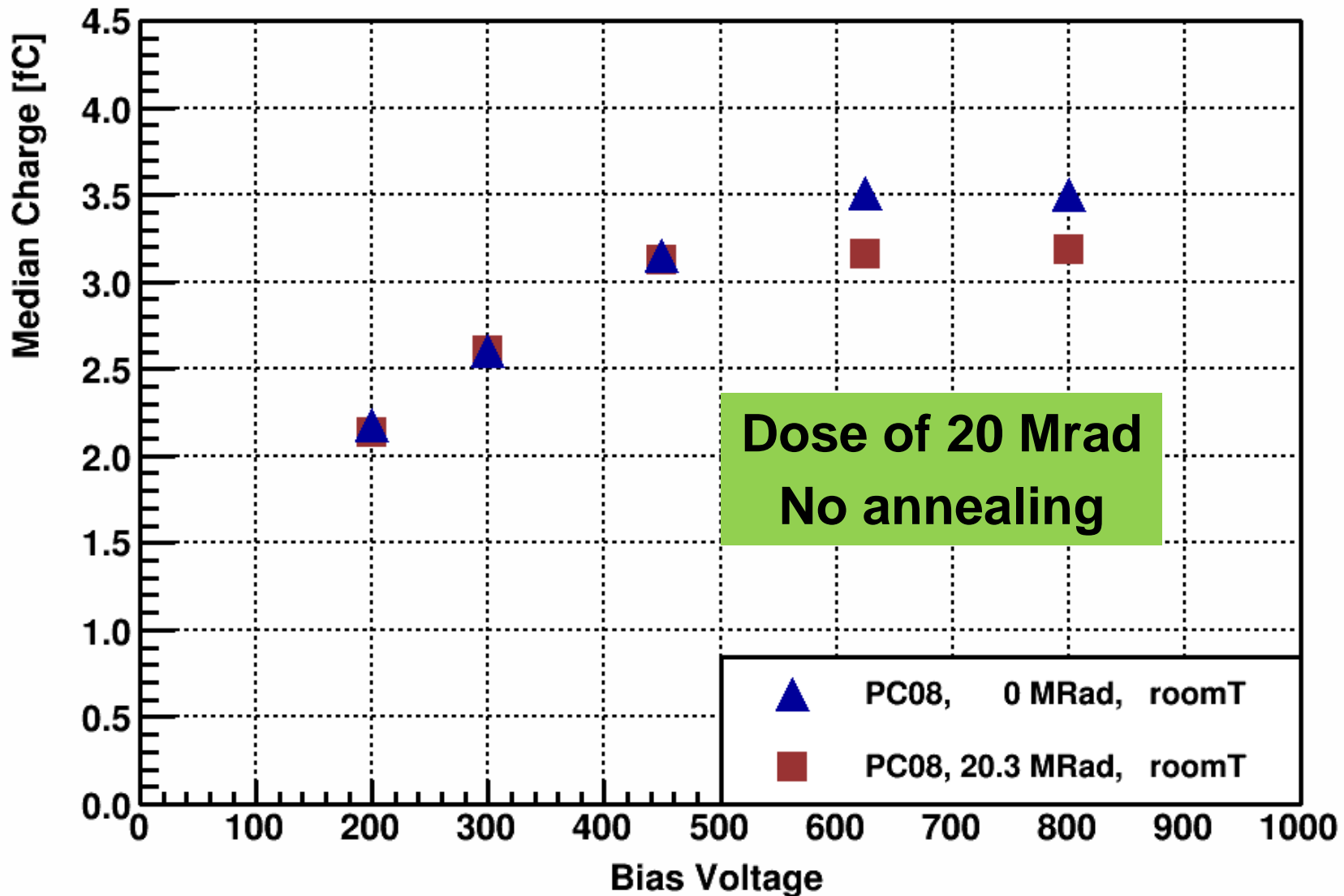
# Results: PF sensors

Median Charge vs Bias Voltage, P-type Float Zone sensors



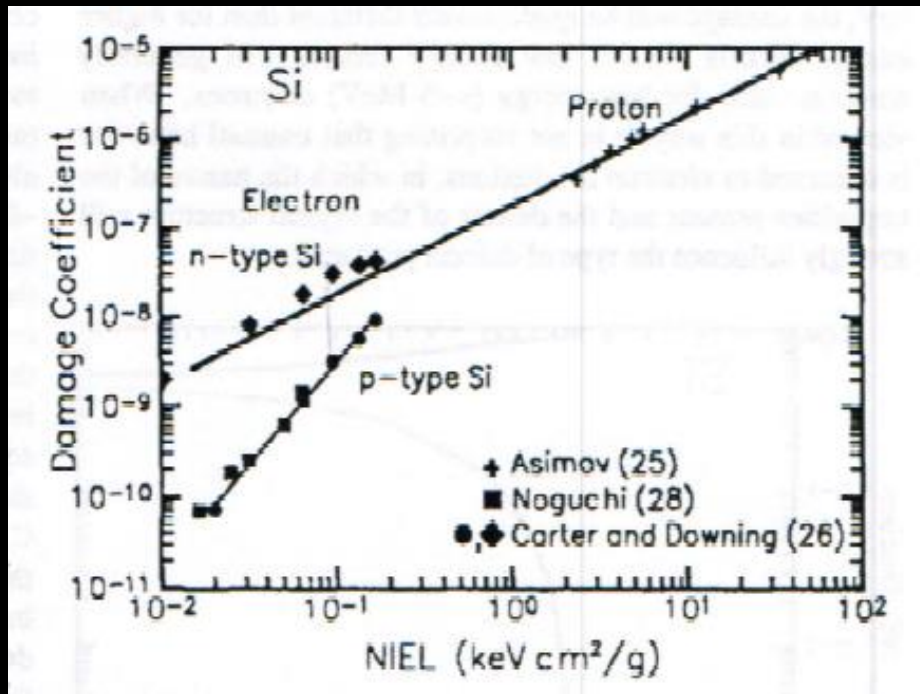
# Results: PC sensors

Median Charge vs Bias Voltage, P-type Magnetic Czochralski sensors





# Departure from NIEL (non-ionizing energy-loss) scaling observed for electron irradiation



NIEL    e<sup>-</sup> Energy

$2 \times 10^{-2}$     0.5 MeV

$5 \times 10^{-2}$     2 MeV

$1 \times 10^{-1}$     10 MeV

$2 \times 10^{-1}$     200 MeV

G.P. Summers et al., IEEE Trans Nucl Sci **40**, 1372 (1993)

**Also: for ~50 MRad illumination of 900 MeV electrons, little loss of charge collection seen for wide variety of sensors [S. Dittongo et al., NIM A 530, 110 (2004)]**

**But what about the hadronic component of EM shower?**

# Results: NF sensor for low dose

